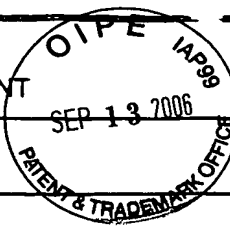


Form PTO 1449  
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## LIST OF REFERENCES CITED BY APPLICANT

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## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	4,792,958	12/20/88	OHBA, et al.			
	AB	4,809,287	02/28/89	OHBA, et al.			
	AC	4,835,117	05/30/89	OHBA, et al.			
	AD	4,949,349	08/14/90	OHBA, et al.			
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	AM	5,079,184	01/07/92	HATANO, et al.			
	AN	5,103,271	04/07/92	IZUMIYA, et al.			

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
	AO	2000-31588	01/28/00	JAPAN		
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					
	AV					

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

AW	Y. OHBA, et al., Japanese Journal of Applied Physics, Vol. 37 Part 2, No. 8A, pp. L 905 - L 906, "FABRICATION AND CHARACTERIZATION OF AlGaIn/GaN DOUBLE-HETEROLASER STRUCTURES ON SAPPHIRE SUBSTRATES USING SINGLE CRYSTALLINE AlN BUFFER LAYERS," August 1, 1998.
AX	
AY	
AZ	<input type="checkbox"/> Additional References sheet(s) attached

Examiner

Date Considered

\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Yasuo OHBA			
				FILING DATE July 5, 2002		GROUP	
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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>[initials]</i>	AA	6,242,764	06/05/2001	Y. OHBA, et al.			
<i>[initials]</i>	AB	5,990,495	11/23/99	Y. OHBA			
<i>[initials]</i>	AC	5,656,832	08/12/97	Y. OHBA, et al.			
<i>[initials]</i>	AD	5,909,040	06/01/99	Y. OHBA, et al.			
<i>[initials]</i>	AE	5,929,466	07/27/99	Y. OHBA, et al.			
	AF						
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FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
<i>[initials]</i>	AO	2000-31588	01/28/2000	JAPAN (with English Abstract)			X
	AP						
	AQ						
	AR						
	AS						
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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
<i>[initials]</i>	AW	Y. OHBA, et al., Japanese Journal of Applied Physics, Vol. 37 Part 2, No. 8A, pps. L 905-L 906, "FABRICATION AND CHARACTERIZATION OF AlGaIn/GaN DOUBLE-HETEROLASER STRUCTURES ON SAPPHIRE SUBSTRATES USING SINGLE CRYSTALLINE AlN BUFFER LAYERS," August 1, 1998					
	AX						
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	AZ						
Examiner J. MONDT <i>[signature]</i>					<input type="checkbox"/> Additional References sheet(s) attached Date Considered 02/05/03.		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

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